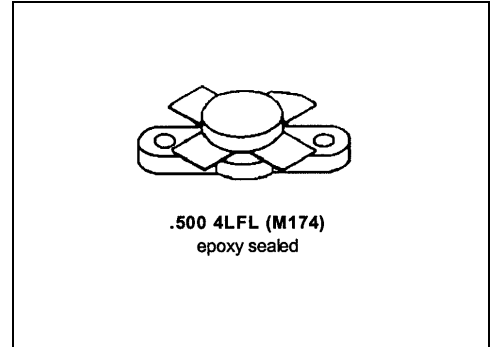


# MS1000

## RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

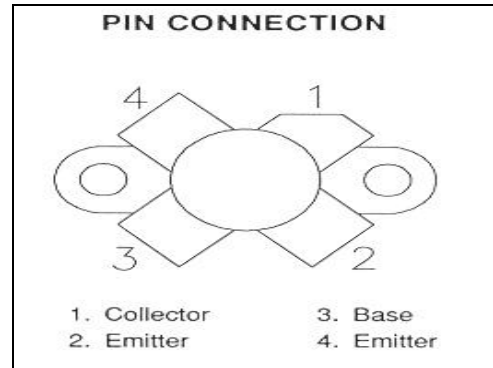
### Features

- 30 MHz
- 28 VOLTS
- IMD = -30 dB
- GOLD METALLIZATION
- P<sub>OUT</sub> = 125 WATTS
- G<sub>P</sub> = 15dB MINIMUM
- COMMON EMITTER CONFIGURATION



### DESCRIPTION:

The MS1000 is a 28V Class A silicon NPN planar transistor designed primarily for SSB communications. Diffused emitter ballast provide infinite VSWR capability under rated operating conditions.



### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	65	V
V <sub>CEO</sub>	Collector-Emitter Voltage	36	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Device Current	20	A
P <sub>D</sub>	Power Dissipation	270	W
T <sub>j</sub>	Junction Temperature	200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

### Thermal Data

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	0.65	°C/W
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**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**
**STATIC**

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
<b>BV<sub>CBO</sub></b>	<b>I<sub>C</sub> = 100 mA</b>	<b>I<sub>E</sub> = 0 mA</b>	<b>65</b>	---	---	<b>V</b>
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 100 mA</b>	<b>V<sub>BE</sub> = 0 V</b>	<b>65</b>	---	---	<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 100 mA</b>	<b>I<sub>B</sub> = 0 mA</b>	<b>35</b>	---	---	<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 10 mA</b>	<b>I<sub>C</sub> = 0 mA</b>	<b>4.0</b>	---	---	<b>V</b>
<b>I<sub>CES</sub></b>	<b>V<sub>CE</sub> = 30 V</b>	<b>I<sub>E</sub> = 0 mA</b>	---	---	<b>15</b>	<b>mA</b>
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V</b>	<b>I<sub>C</sub> = 5 A</b>	<b>10</b>	---	<b>200</b>	---

**DYNAMIC**

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 30MHz</b>	<b>P<sub>IN</sub> = 3.95W</b>	<b>V<sub>CE</sub> = 28V</b>	<b>125</b>	---	---	<b>W</b>
<b>G<sub>P</sub></b>	<b>f = 30MHz</b>	<b>P<sub>IN</sub> = 3.95W</b>	<b>V<sub>CE</sub> = 28V</b>	<b>15</b>	---	---	<b>dB</b>
<b>IMD*</b>	<b>f = 30MHz</b>	<b>V<sub>CC</sub> = 28V</b>	<b>I<sub>CQ</sub> = 100mA</b>	---	---	<b>-30</b>	<b>dB</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz</b>	<b>V<sub>CB</sub> = 30V</b>		---	---	<b>285</b>	<b>pf</b>

\* TWO-TONE MEASUREMENT

**PACKAGE MECHANICAL DATA**

